Semiconductor Lasers - Principles and Current Research

Managing Director of the Institute of Applied Physics
Faculty of Physics and Astronomy

ECTS: 6
Method of grading: Only after succ. compl. of module(s)
Numerical grade: --

Duration: 1 semester
Module level: graduate
Other prerequisites: Certain prerequisites must be met to qualify for admission to assessment. The lecturer will inform students about the respective details at the beginning of the course. Registration for the course will be considered a declaration of will to seek admission to assessment. If students have obtained the qualification for admission to assessment over the course of the semester, the lecturer will put their registration for assessment into effect. Students who meet all prerequisites will be admitted to assessment in the current or in the subsequent semester. For assessment at a later date, students will have to obtain the qualification for admission to assessment anew.

Contents
This lecture discusses the principles of laser physics, based on the example of semiconductor lasers, and current developments regarding components. The principles of lasers are described on the basis of a general laser model, which will then be extended to special aspects of semiconductor lasers. Basic concepts such as threshold condition, characteristic curve and laser efficiency are derived from coupled rate equations for charge carriers and photons. Other topics of the lecture are optical processes in semiconductors, layer and ridge waveguides, laser resonators, mode selection, dynamic properties as well as technology for the generation of semiconductor lasers. The lecture closes with current topics of laser research such as quantum dot lasers, quantum cascade lasers, terahertz lasers or high-performance lasers.

Intended learning outcomes
The students have advanced knowledge of the principles of semiconductor-laser physics. They can apply their knowledge to modern questions and know the applications in the current development of components.

Courses
R + V (no information on SWS (weekly contact hours) and course language available)

Method of assessment
a) written examination (approx. 90 minutes) or b) oral examination of one candidate each or oral examination in groups (approx. 30 minutes per candidate, for modules with less than 4 ECTS credits approx. 20 minutes) or c) project report (approx. 8 to 10 pages, time to complete: 1 to 4 weeks) or d) presentation/seminar presentation (approx. 30 minutes)
Assessment offered: When and how often assessment will be offered depends on the method of assessment and will be announced in due form under observance of Section 32 Subsection 3 ASPO (general academic and examination regulations) 2009.
Language of assessment: German, English

Allocation of places
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Additional information
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Referred to in LPO I (examination regulations for teaching-degree programmes)
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Module appears in
Bachelor’ degree (1 major) Physics (2010)
Bachelor's degree (1 major) Physics (2012)
Bachelor's degree (1 major) Nanostructure Technology (2010)
Bachelor's degree (1 major) Nanostructure Technology (2012)
Master's degree (1 major) Mathematics (2012)
Master's degree (1 major) Physics (2010)
Master's degree (1 major) Physics (2011)
Master's degree (1 major) Nanostructure Technology (2011)
Master's degree (1 major) Nanostructure Technology (2010)
Master's degree (1 major) FOKUS Physics - Nanostructuring Technology (2010)
Master's degree (1 major) FOKUS Physics (2010)
Master's degree (1 major) FOKUS Physics (2011)
Master's degree (1 major) Computational Mathematics (2012)
Master's degree (1 major) Functional Materials (2012)